2. (Previously Amended) The apparatus of claim 1 wherein said stainless steel alloy has at least 15% chromium.

3. (Previously Amended) The apparatus of claim 1 wherein said stainless steel has alloy has less than 1% nickel.

4. (Previously Amended) The apparatus of claim 1 wherein said stainless steel alloy is selected from the group consisting of stainless steel alloy 430, stainless steel alloy 440, and stainless steel alloy 446.

5. (Unchanged) The apparatus of claim 1 wherein said phosphorous precursor compound is TEPO, TMP or TEP.

6. (Unchanged) The apparatus of claim 1 wherein said phosphorous precursor is TMP.

7. (Unchanged) The apparatus of claim 1 wherein said phosphorous precursor compound is TEP.

8. (Previously Amended) An apparatus for delivering a liquid phosphorous precursor compound, comprising:

a container adapted to hold said liquid phosphorous precursor compound;

a conduit configured to convey said liquid phosphorous precursor compound or a gaseous product of said liquid phosphorous precursor compound from the container;

a heating surface coupled to at least one of a portion of said container and a portion of said conduit;

wherein at least one of said portion of said container and said portion of said conduit is composed of a stainless steel alloy having less than 5 percent nickel.

9. (Previously Amended) The apparatus of claim 8 wherein said stainless steel alloy comprises at least 15% chromium.

10. (Previously Amended) The apparatus of claim 8 wherein said stainless steel alloy comprises less than 1% nickel.

11. (Previously Amended) The apparatus of claim 8 wherein said stainless steel alloy is selected from the group consisting of stainless steel alloy 430, stainless steel alloy 440, and stainless steel alloy 446.

12. (Unchanged) The apparatus of claim 8 further comprising a heater for heating said heating surface to a temperature of 160-170 degrees Celsius.

13. (Unchanged) The apparatus of claim 8 wherein said apparatus is a bubbler system for delivering gases to a chemical reaction chamber for semiconductor wafers.

14. (Unchanged) The apparatus of claim 8 wherein said apparatus is a boiler system for delivering gases to a chemical reaction chamber for semiconductor wafers.

15. (Previously Amended) The apparatus of claim 8 wherein said apparatus comprises an injection system for delivering gases to a chemical reaction chamber for semiconductor wafer fabrication, and wherein said injection system includes an injection valve composed of a stainless steel alloy having less than 5 percent nickel.

16. (Previously Amended) The apparatus of claim 8 wherein said portion composed of the stainless steel alloy comprises a gasket and a seal.

17. (Unchanged) The apparatus of claim 8 wherein said phosphorous precursor compound is TEPO, TMP or TEP.

18. (Unchanged) The apparatus of claim 8 wherein said phosphorous precursor is TMP.

19. (Unchanged) The apparatus of claim 8 wherein said phosphorous precursor compound is TEP.

20. (Previously Amended) A liquid flow injection valve for supplying TEPO, TMP or TEP to a chemical vapor deposition (CVD) chamber comprising:

an injection orifice for connecting to a source of liquid TEPO, TMP or TEP; and

a valve outlet for delivering a gaseous mixture generated from said liquid TEPO, TMP or TEP to said CVD chamber;

said injection orifice including a stainless steel alloy having less than 5% nickel.

21. (Previously Amended) The valve of claim 20 wherein said stainless steel alloy has at least 15% chromium.

22. (Previously Amended) The valve of claim 20 wherein said stainless steel alloy is selected from the group consisting of stainless steel alloy 430, stainless steel alloy 440, and stainless steel alloy 446.

23. (Unchanged) The valve of claim 20 further comprising a heater for heating said valve to a temperature of 160-170 degrees Celsius.

24. (Unchanged) The valve of claim 20 further comprising a plug in said valve composed of a polyamide.

25. (Unchanged) The valve of claim 24 wherein said polyamide is Vespel.

26. (Unchanged) A liquid injection system for a CVD chamber comprising:

a container for holding liquid TEPO, TMP or TEP;

an injection valve for converting said liquid TEPO, TMP or TEP into gaseous form, said injection valve having portions in contact with said liquid TEPO, TMP or TEP composed of a stainless steel alloy having less then 5% nickel and at least 15% chromium;

a liquid TEPO, TMP or TEP injection line coupling said container to said injection valve;

a carrier gas source line coupled to said injection valve; and

an outlet line coupling said injection valve to said CVD chamber.

27. (Unchanged) The system of claim 26 wherein said stainless steel alloy is one of stainless steel alloys 430, 440 and 446.

28. (Unchanged) A method for injecting gaseous phosphorous precursor into a chemical vapor deposition chamber, the method comprising:

providing a liquid TEPO, TMP or TEP through an injection valve including a stainless steel alloy having less than 10% nickel;

providing a carrier gas through said valve;

creating a pressure differential in said valve; and

heating said injection valve.

29. (Unchanged) The method of claim 28 further comprising the step of heating said valve to a temperature of 160-170 degrees Celsius.

30. (Unchanged) The method of claim 29 wherein said valve is heated to approximately 165 degrees Celsius.

31-45. PREVIOUSLY CANCELED

46. An apparatus for use with a liquid phosphorous precursor compound, the apparatus comprising:

a container adapted to [hld] hold the liquid phosphorous precursor compound;

a conduit; and

an orifice disposed between the liquid container and the conduit, wherein at least one of the liquid container, the orifice, and the conduit has a surface of a stainless steel alloy having less than 10 % nickel.

B2 (150)

REMARKS

Claim 46 has been amended; and claims 1-30 remain unchanged. Thus, claims 1-30 and 46 are pending.